



P3M12080K4 SiC MOS N-Channel Enhancement Mode

V_{RRM}	= 1200	V
I_D	= 38	A
$I_D (100^\circ\text{C})$	= 27	A
$R_{DS(on)}$	= 80	m Ω

SiC MOS P3M12080K4 N-Channel Enhancement Mode

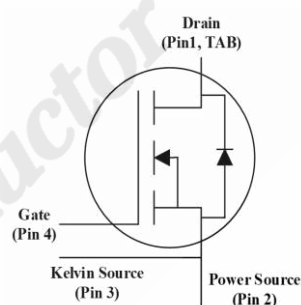
Features

- Qualified to AEC-Q101
- High Blocking Voltage with Low On-Resistance
- High-Frequency Operation
- Ultra-Small Q_{gd}
- 100% UIS tested



Benefits

- Improve System Efficiency
- Increase Power Density
- Reduce Heat Sink Requirements
- Reduction of System Cost



TO-247-4

Drain	1
Power Source	2
Kelvin Source	3
Gate	4

Applications

- Solar Inverters
- EV Battery Chargers
- High Voltage DC/DC Converters
- Switch Mode Power Supplies



Order Information

Part Number	Package	Marking
P3M12080K4	TO-247-4	P3M12080K4



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P3M12080K4 SiC MOS N-Channel Enhancement Mode

1. Maximum Ratings

At $T_J = 25^\circ\text{C}$, unless specified otherwise

Parameter	Symbol	Value	Unit	Test Conditions
Drain - Source Voltage	V_{DSmax}	1200	V	$V_{GS} = 0V$ $I_D = 100\mu A$
Gate - Source Voltage (dynamic)	V_{GSmax}	-8 / +21	V	AC (f > 1Hz)
Gate - Source Voltage(static) turn-on gate voltage turn-off gate voltage	$V_{GS,on}$ $V_{GS,off}$	+15 / +18 -3	V	Static
Continuous Drain Current	I_D	38	A	$V_{GS} = 15V$ $T_C = 25^\circ\text{C}$
		27		$V_{GS} = 15V$ $T_C = 100^\circ\text{C}$
Pulsed Drain Current	$I_{D(pulse)}$	80	A	
Power Dissipation	P_D	221	W	
Operating Junction	T_J	-55 To +175	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-55 To +175	$^\circ\text{C}$	
Solder Temperature	T_L	260	$^\circ\text{C}$	
Mounting Torque	M_d	1 8.8	Nm lbf-in	M3 or 6-32 screw



2. Electrical Characteristics

At $T_J = 25^\circ\text{C}$, unless specified otherwise

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200	/	/	V	$V_{GS} = 0V$ $I_D = 100\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.4	/	V	(tested after 30ms pulse at $V_{GS} = 15V$) $V_{DS} = V_{GS}$ $I_D = 5mA$ $T_J = 25^\circ\text{C}$
		/	1.6	/	V	$V_{DS} = V_{GS}$ $I_D = 5mA$ $T_J = 175^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	/	1.8	100	μA	$V_{GS} = 0V$ $V_{DS} = 1200V$
Gate-Source Leakage Current	I_{GSS}	/	20	250	nA	$V_{GS} = 15V$ $V_{DS} = 0V$
Drain-Source On-State Resistance	$R_{DS(on)}$	/	80	104	m Ω	$V_{GS} = 15V$ $I_D = 20A$ $T_J = 25^\circ\text{C}$
		/	104	/		$V_{GS} = 15V$ $I_D = 20A$ $T_J = 175^\circ\text{C}$
		/	66	/		$V_{GS} = 18V$ $I_D = 20A$ $T_J = 25^\circ\text{C}$



P3M12080K4 SiC MOS

N-Channel Enhancement Mode

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Transconductance	g_{fs}	/	10	/	S	$V_{DS} = 20V$ $I_{DS} = 20A$ $T_J = 25^{\circ}C$
		/	9.6	/		$V_{DS} = 20V$ $I_{DS} = 20A$ $T_J = 175^{\circ}C$
Input Capacitance	C_{iss}	/	2032	/	pF	$V_{GS} = 0V$ $V_{DS} = 800V$ $f = 1MHz$ $V_{AC} = 25mV$
Output Capacitance	C_{oss}	/	73.6	/		
Reverse Transfer Capacitance	C_{rss}	/	6	/		
Coss Stored Energy	E_{oss}	/	52.9	/	μJ	
Turn-on Energy	E_{on}	/	312	/	μJ	$V_{DS} = 800V$ $V_{GS} = -3/15V$ $I_D = 20A$ $R_G = 1\Omega$
Turn-off Energy	E_{off}	/	34	/		
Turn-on Energy	E_{on}	/	237	/	μJ	$V_{DS} = 800V$ $V_{GS} = -3/18V$ $I_D = 20A$ $R_G = 1\Omega$
Turn-off Energy	E_{off}	/	35	/		
Turn-On Delay Time	$t_{d(on)}$	/	16	/	ns	$V_{DS} = 800V$ $V_{GS} = -3/15V$ $I_D = 20A$ $R_G = 1\Omega$
Rise Time	t_r	/	20	/		
Turn-Off Delay Time	$t_{d(off)}$	/	21	/		
Fall Time	t_f	/	17	/		
Internal Gate Resistance	$R_{G(int)}$	/	3.5	/	Ω	$f = 1MHz$ $V_{AC} = 25mV$



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Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Gate to Source Charge	Q_{gs}	/	22.2	/	nC	$V_{DS} = 800V$ $I_{DS} = 20A$ $V_{GS} = -3 \text{ to } 15V$ $I_G = 20mA$
Gate to Drain Charge	Q_{gd}	/	12.3	/		
Total Gate Charge	Q_g	/	54.6	/		

3. Reverse Diode Characteristics

At $T_J = 25^\circ C$, unless specified otherwise

Parameter	Symbol	Value		Unit	Test Conditions
		Typ.	Max.		
Diode Forward Voltage	V_{SD}	5.2	/	V	$V_{GS} = -3V$ $I_{SD} = 10A$ $T_J = 25^\circ C$
		4.8	/	V	$V_{GS} = -3V$ $I_{SD} = 10A$ $T_J = 175^\circ C$
Continuous Diode Forward Current	I_S	31	/	A	$V_{GS} = -3V$
Reverse Recover Time	t_{rr}	16	/	ns	$V_{GS} = -3V$ $I_{SD} = 20A$ $V_R = 800V$ $di_f/dt = 4500A/\mu s$ $T_J = 25^\circ C$
Reverse Recovery Charge	Q_{rr}	377	/	nC	
Peak Reverse Recovery Current	I_{rrm}	41	/	A	

Parameter	Symbol	Value		Unit	Test Conditions
		Typ.	Max.		
Reverse Recover Time	t_{rr}	15	/	ns	$V_{GS} = -3V$ $I_{SD} = 20A$ $V_R = 800V$ $d_{if}/d_t = 4100A/\mu s$ $T_J = 25^\circ C$
Reverse Recovery Charge	Q_{rr}	447	/	nC	
Peak Reverse Recovery Current	I_{rrm}	51	/	A	

4. Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.68	$^\circ C/W$

5. Typical Performance

At $T_J = 25^\circ C$, unless specified otherwise

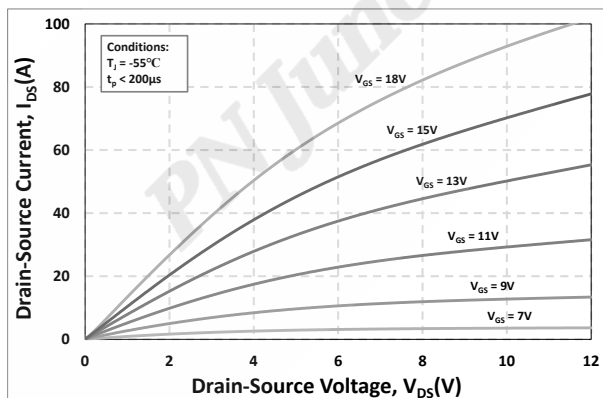


Figure 1. Output Characteristics $T_J = -55^\circ C$

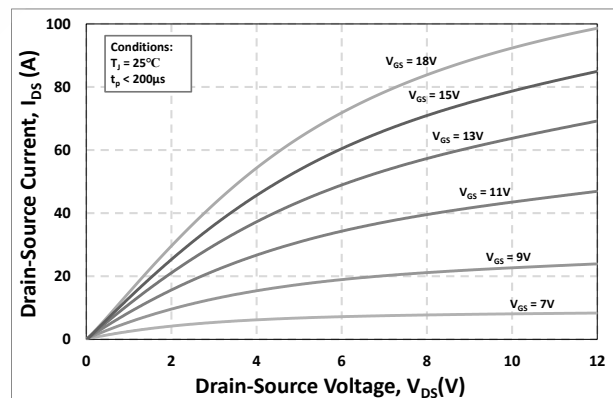


Figure 2. Output Characteristics $T_J = 25^\circ C$

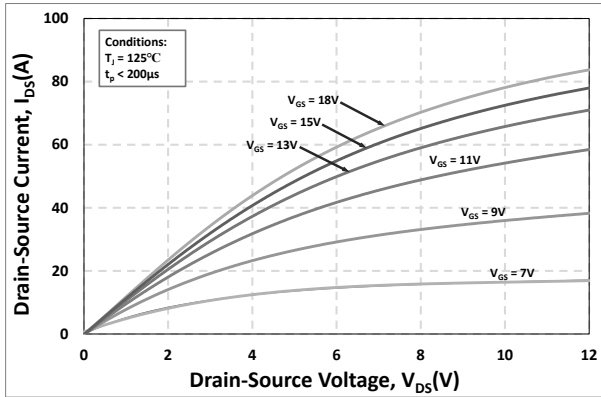


Figure 3. Output Characteristics $T_J = 125^\circ\text{C}$

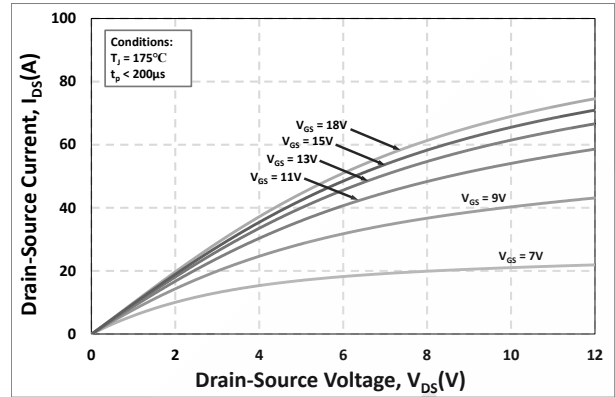


Figure 4. Output Characteristics $T_J = 175^\circ\text{C}$

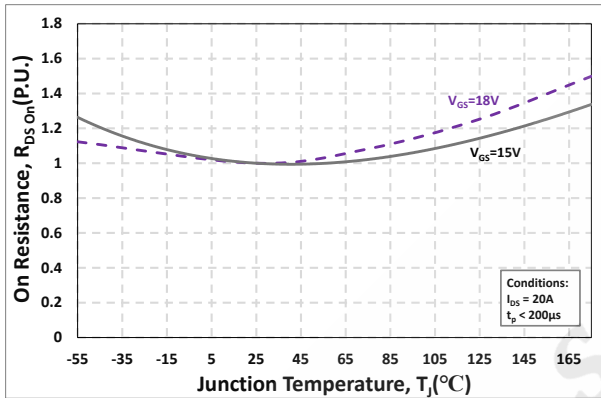


Figure 5. Normalized On-Resistance vs. Temperature

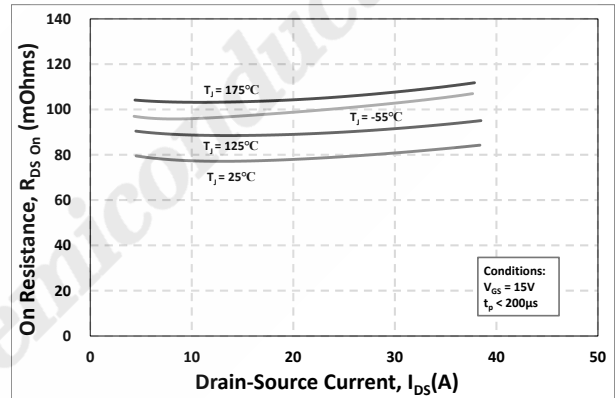


Figure 6. On-Resistance vs. Drain Current Various Temperatures

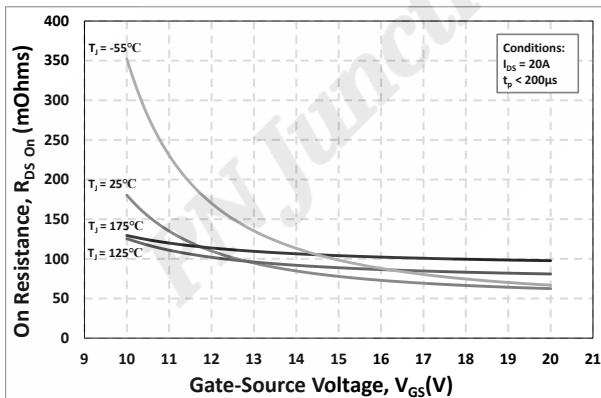


Figure 7. On-Resistance vs. Gate-Source Voltage

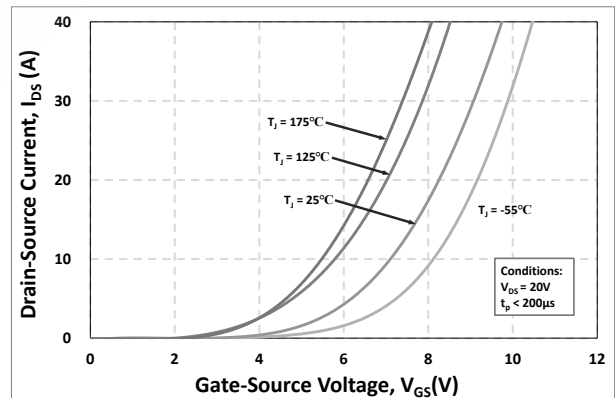


Figure 8. Transfer Characteristic for Various Junction Temperatures

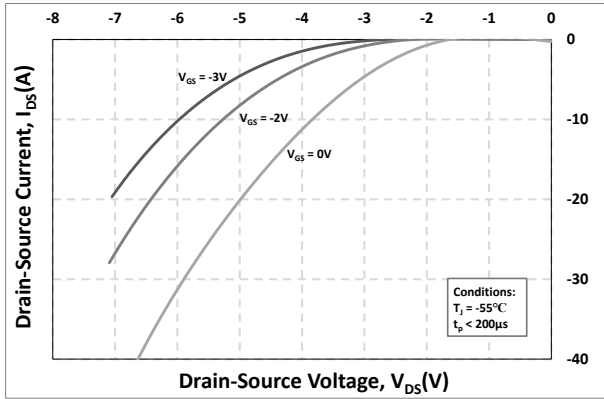


Figure 9. Body Diode Characteristic at -55°C

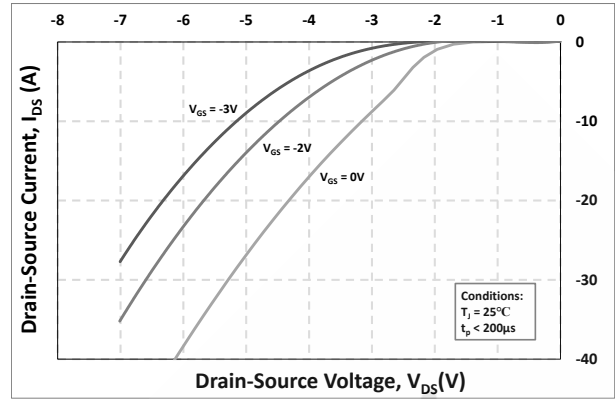


Figure 10. Body Diode Characteristic at 25°C

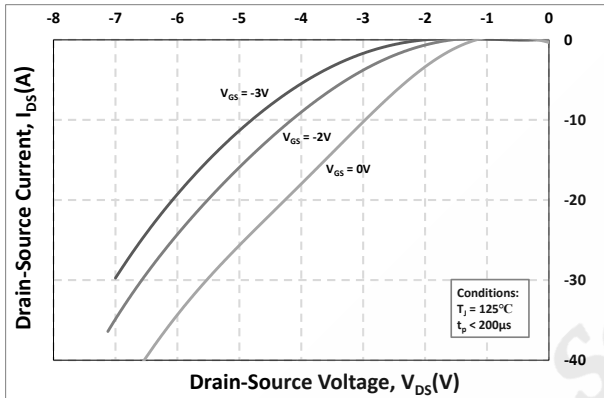


Figure 11. Body Diode Characteristic at 125°C

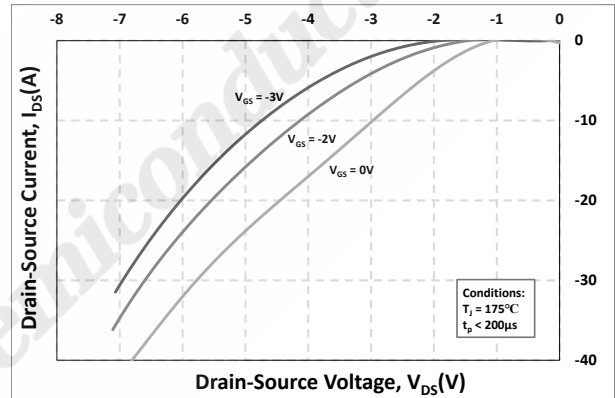


Figure 12. Body Diode Characteristic at 175°C

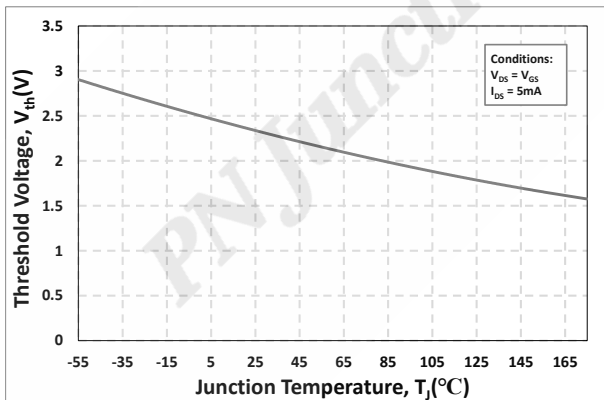


Figure 13. Threshold Voltage vs. Temperature

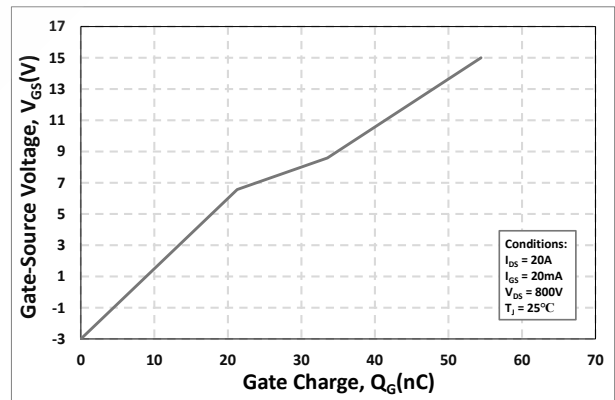


Figure 14. Gate Charge Characteristics

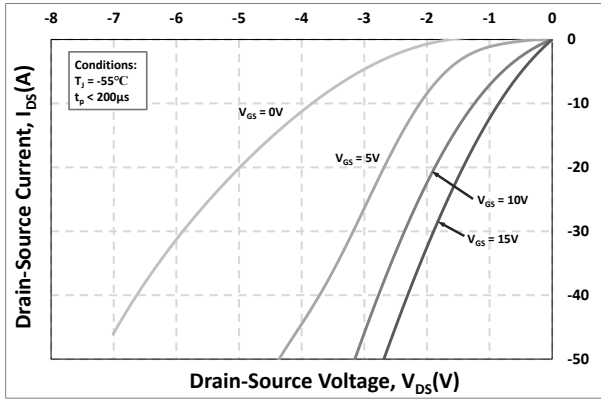


Figure 15. 3rd Quadrant Characteristic at -55°C

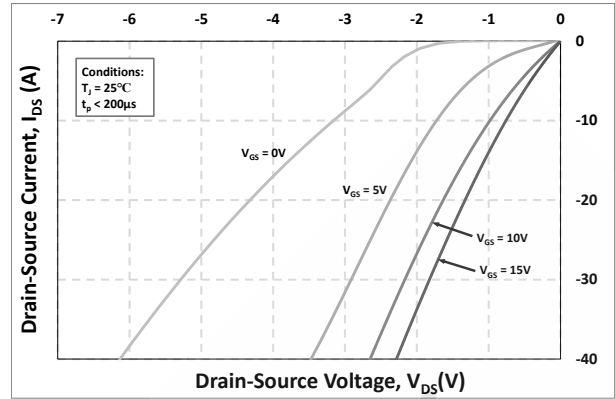


Figure 16. 3rd Quadrant Characteristic at 25°C

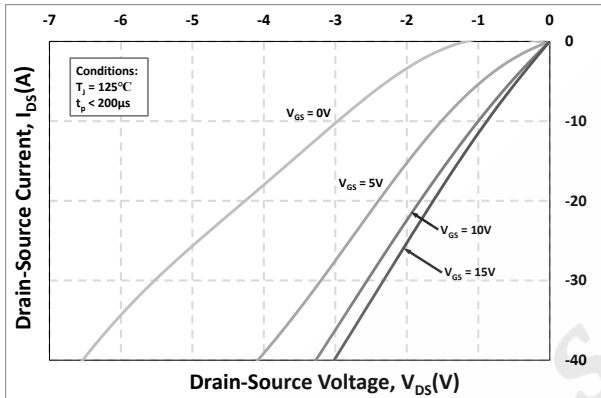


Figure 17. 3rd Quadrant Characteristic at 125°C

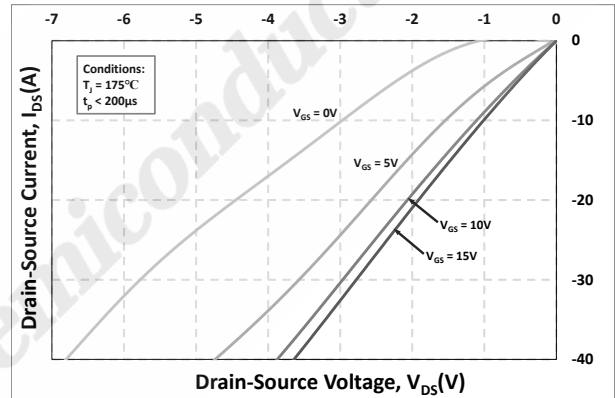


Figure 18. 3rd Quadrant Characteristic at 175°C

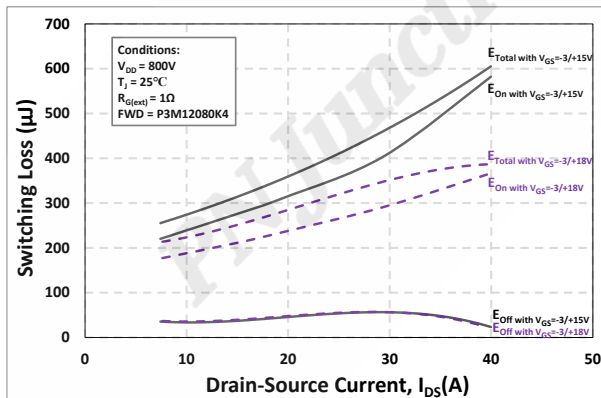


Figure 19. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 800V$)

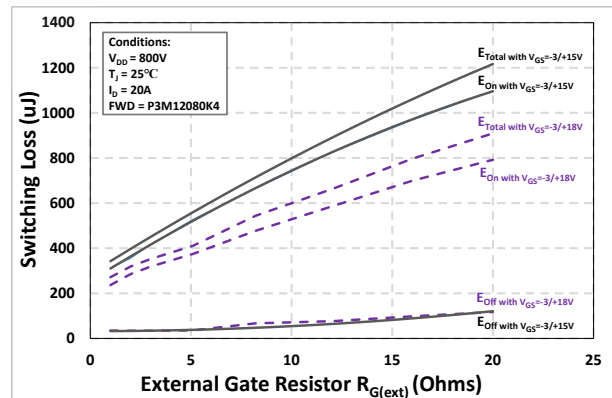


Figure 20. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

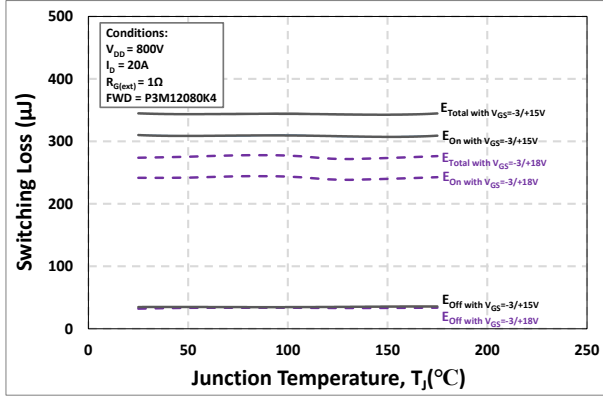


Figure 21. Clamped Inductive Switching Energy vs. Temperature

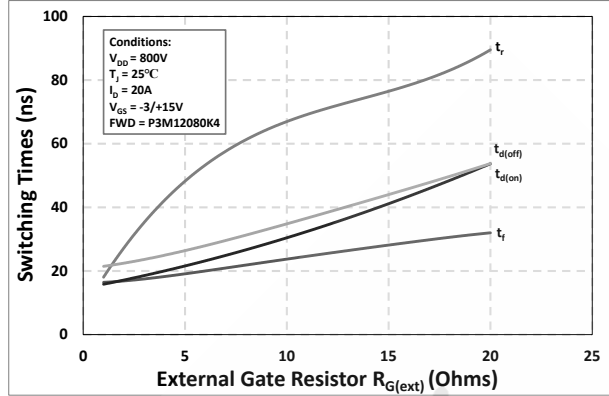


Figure 22. Switching Times vs. $R_{G(ext)}$

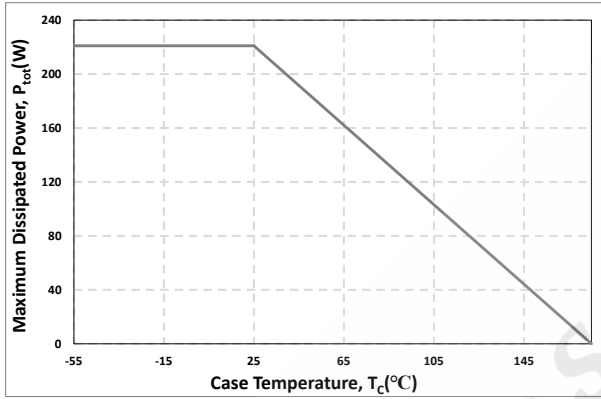


Figure 23. Maximum Power Dissipation Derating vs. Case Temperature

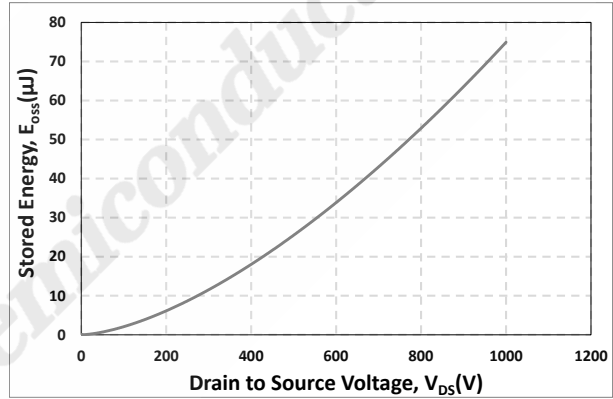


Figure 24. Output Capacitor Stored Energy

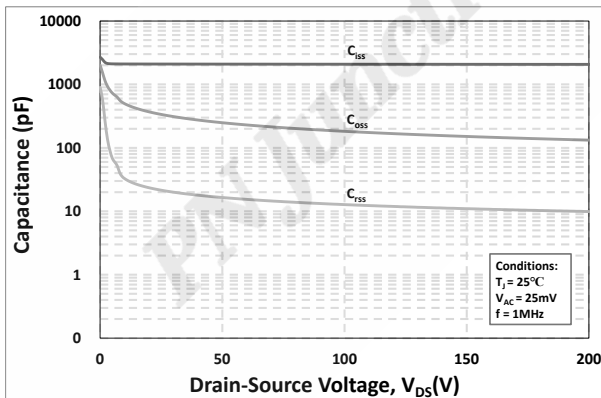


Figure 25. Capacitances vs. Drain-Source Voltage (0 - 200V)

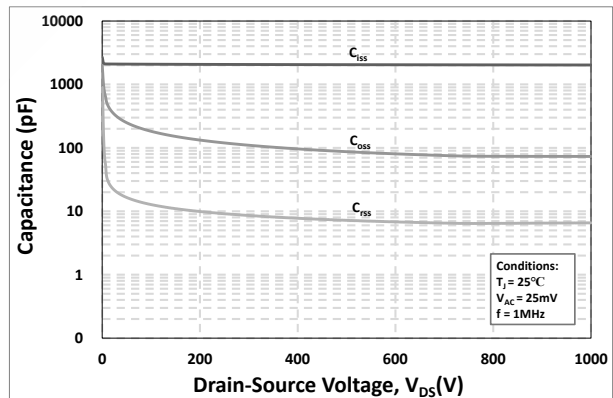


Figure 26. Capacitances vs. Drain-Source Voltage (0 - 1000V)

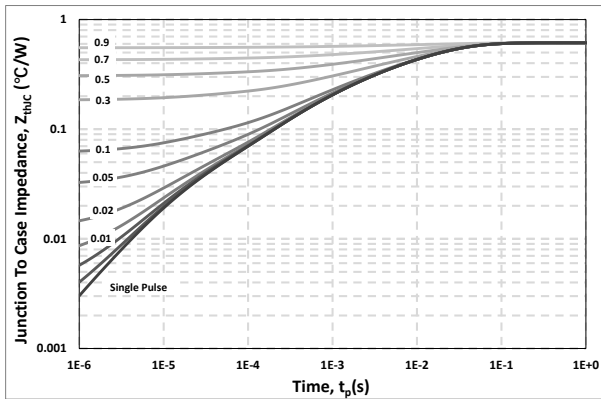


Figure 27. Transient Thermal Impedance (Junction - Case)

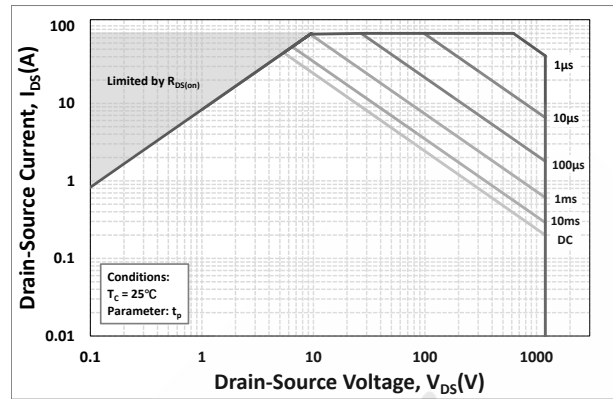


Figure 28. Safe Operating Area

6. Definitions

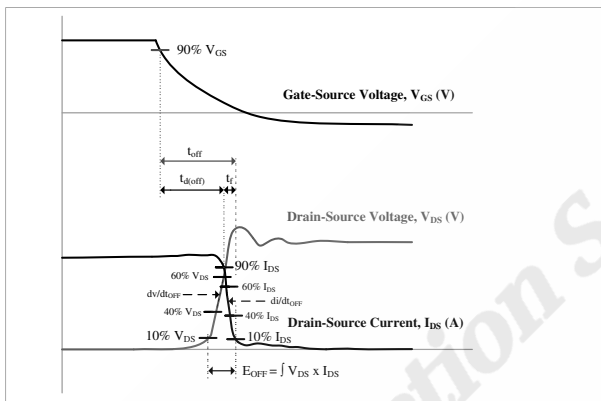


Figure 29. Turn-off Transient Definitions

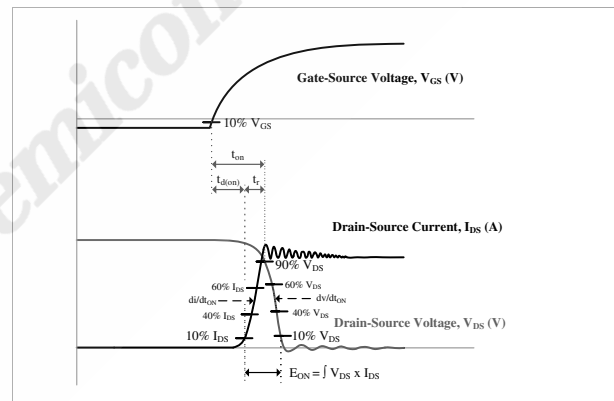


Figure 30. Turn-on Transient Definitions

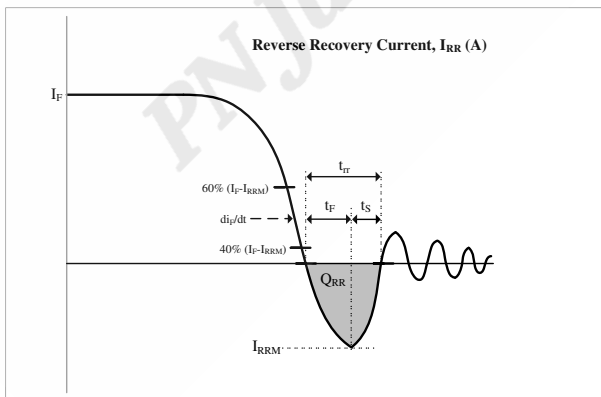


Figure 31. Reverse Recovery Definitions

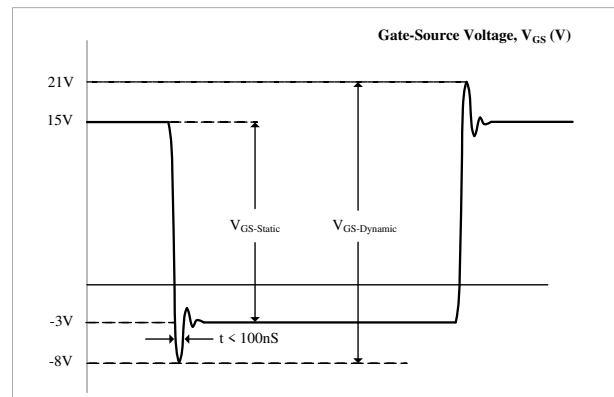
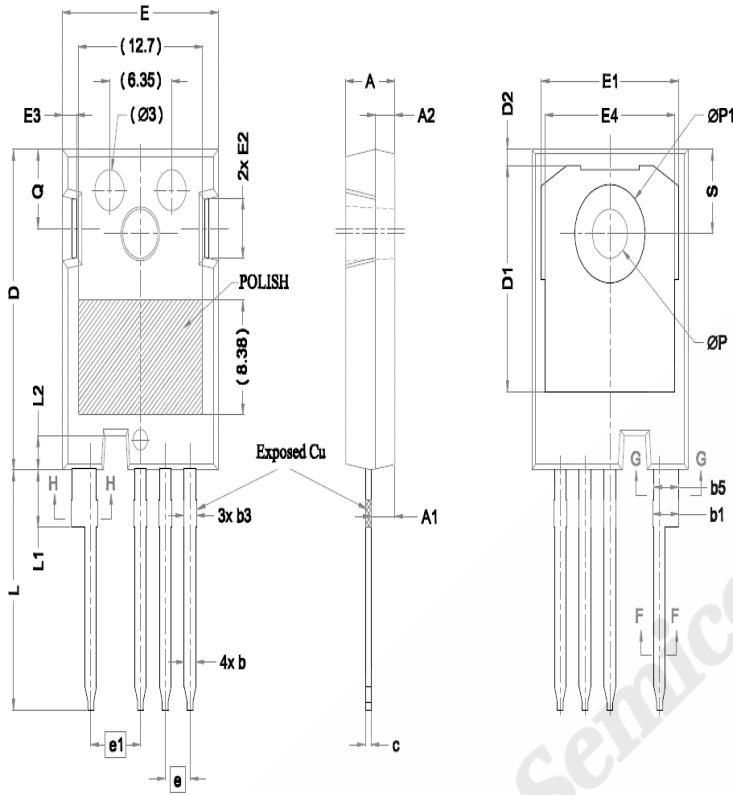


Figure 32. v_{GS} Transient Definitions

7. Package Outlines



Symbol	Dimensions		
	Min.	Nom.	Max.
A	4.83	5.02	5.21
A1	2.28	2.41	2.54
A2	1.91	2.00	2.16
b ¹	1.07	1.20	1.28
b	1.07	1.20	1.33
b1	2.39	2.67	2.94
b2	2.39	2.67	2.84
b3	1.07	1.30	1.60
b4	1.07	1.30	1.50
b5	2.39	2.53	2.69
b6	2.39	2.53	2.64
c	0.55	0.60	0.68
c1	0.55	0.60	0.65
D	22.30	23.45	23.80
D1	16.25	16.55	17.65
D2	0.95	1.19	1.25
E	15.75	15.94	16.13
E1	13.10	14.02	14.15
E2	3.60	1.10	5.10
E3	1.00	1.45	1.90
E4	12.38	13.26	13.43
e	2.54BSC		
e1	5.08BSC		
L	17.31	17.57	17.82
L1	3.97	4.19	4.37
L2	2.35	2.50	2.65
ØP	3.51	3.61	3.65
ØP	7.19 REF.		
Q	5.49	5.79	6.00
S	6.04	6.17	6.30

Drawing and Dimensions

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